

IN THE CLAIMS:

Please amend the claims as follows:

1. (Previously Presented) An electrode structure for a display device having at least one emitter, comprising:
a first electrode located adjacent the at least one emitter;
a second electrode; and
an insulating layer disposed between the first electrode and the second electrode including a ridge located closer to the at least one emitter than a portion of the first electrode or a portion of the second electrode.
2. (Original) The electrode structure of claim 1, wherein the second electrode comprises a layer of conductive material disposed on a plane over the insulating layer, and the first electrode comprises a layer of conductive material disposed on a plane under the insulating layer.
3. (Original) The electrode structure of claim 2, wherein the first electrode is a gate electrode and the second electrode is a focusing electrode.
4. (Original) The electrode structure of claim 3, wherein the insulating layer comprises silicon oxide.
5. (Original) The electrode structure of claim 1, wherein a second insulating layer is disposed between the insulating layer and the first electrode.
6. (Original) The electrode structure of claim 5, wherein the second insulating layer comprises silicon nitride.

7. (Previously Presented) The electrode structure of claim 1, wherein the first electrode comprises a first layer of conductive material and the second electrode comprises a second layer of conductive material, the first and second layers of conductive material being disposed on a single plane above the at least one emitter.

8. (Original) The electrode structure of claim 7, wherein the insulating layer further comprises a ridge protruding above an upper surface of the first electrode or the second electrode.

9. (Original) The electrode structure of claim 8, wherein the insulating layer comprises silicon oxide.

10. (Original) The electrode structure of claim 1, wherein at least one of the first electrode and the second electrode comprises polysilicon, titanium, aluminum, or tungsten.

11. (Previously Presented) The electrode structure of claim 2, further comprising: at least one additional insulating layer disposed on a plane over the second electrode; and at least one additional electrode comprising a layer of conductive material disposed on a plane over the at least one additional insulating layer.

12. (Previously Presented) The electrode structure of claim 7, further comprising: at least one additional electrode comprising a layer of conductive material disposed on the single plane above the at least one emitter; and at least one additional insulating layer disposed between the second electrode and the at least one additional electrode.

13. (Currently Amended) A display device, comprising an electrode structure having: a gate electrode located adjacent an emitter; a focusing electrode including a layer of conductive material; and

an insulating layer disposed between the gate electrode and the focusing electrode including a ridge protruding closer to the emitter than one of a sidewall of the gate electrode and a sidewall of the focusing electrode.

14. (Original) The device of claim 13, wherein the focusing electrode comprises a layer of conductive material disposed on a plane over the insulating layer, and the gate electrode comprises a layer of conductive material disposed on a plane under the insulating layer.

15. (Original) The device of claim 14, wherein the insulating layer comprises silicon oxide.

16. (Original) The device of claim 15, wherein a second insulating layer is disposed between the insulating layer and the gate electrode.

17. (Original) The device of claim 16, wherein the second insulating layer comprises silicon nitride.

18. (Previously Presented) The device of claim 13, wherein the gate electrode comprises a first layer of conductive material and the focusing electrode comprises a second layer of conductive material, the first and second layers of conductive material being disposed on a single plane above the emitter.

19. (Original) The device of claim 18, wherein the insulating layer further comprises a ridge protruding above an upper surface of the gate electrode or the focusing electrode.

20. (Original) The device of claim 19, wherein the insulating layer comprises silicon oxide.

21. (Original) The device of claim 13, wherein at least one of the gate electrode and the focusing electrode comprises polysilicon, titanium, aluminum, or tungsten.

22. (Previously Presented) The device of claim 14, further comprising:
at least one additional insulating layer disposed on a plane over the focusing electrode; and
at least one additional electrode comprising a layer of conductive material disposed on a plane over the at least one additional insulating layer.

23. (Original) The device of claim 18, further comprising:
at least one additional electrode comprising a layer of conductive material disposed on the single plane above the emitter; and
at least one additional insulating layer disposed between the focusing electrode and the at least one additional electrode.